

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \text{ max}}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
60V	16m Ω @ $V_{GS} = 10\text{V}$	8.9A
	27m Ω @ $V_{GS} = 4.5\text{V}$	6.8A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Synchronous Rectifiers
- Boost Converters
- Power Management Functions

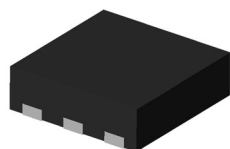
Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm²
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

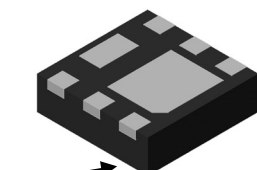
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.007 grams (approximate)

U-DFN2020-6

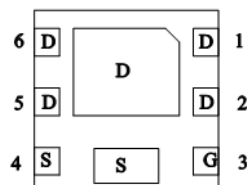
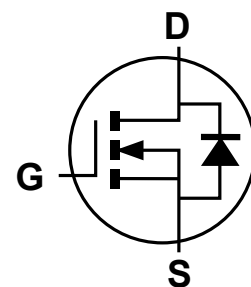


Top View



Pin1

Bottom View


 Pin Out
Bottom View


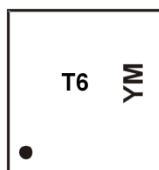
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per reel
DMT6016LFDF-7	T6	7	3,000
DMT6016LFDF-13	T6	13	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



T6 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: A = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	8.9 7.1	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.1 8.9	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	60	A
Maximum Body Diode Continuous Current			I _S	2.2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	15.3	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	11.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.82	W
	T _A = +70°C		0.52	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	153	°C/W
	t < 10s		97	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.9	W
	T _A = +70°C		1.2	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	66	°C/W
	t < 10s		42	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	14.7	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	16	mΩ	V _{GS} = 10V, I _D = 10A
		—	—	27		V _{GS} = 4.5V, I _D = 6A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	864	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	282	—		
Reverse Transfer Capacitance	C _{rss}	—	27.1	—		
Gate Resistance	R _G	—	1.35	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	17	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	8.4	—		
Gate-Source Charge	Q _{gs}	—	3.1	—		
Gate-Drain Charge	Q _{gd}	—	4.3	—		
Turn-On Delay Time	t _{D(on)}	—	3.4	—	nS	V _{GS} = 10V, V _{DD} = 30V, R _G = 6Ω, I _D = 10A
Turn-On Rise Time	t _r	—	5.2	—		
Turn-Off Delay Time	t _{D(off)}	—	12.9	—		
Turn-Off Fall Time	t _f	—	6.8	—		
Body Diode Reverse Recovery Time	t _{rr}	—	22	—	nS	I _S = 10A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	11.1	—	nC	I _S = 10A, dI/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

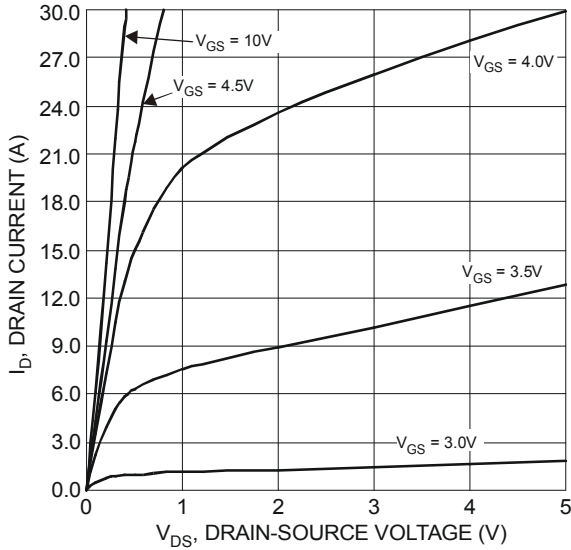


Figure 1 Typical Output Characteristics

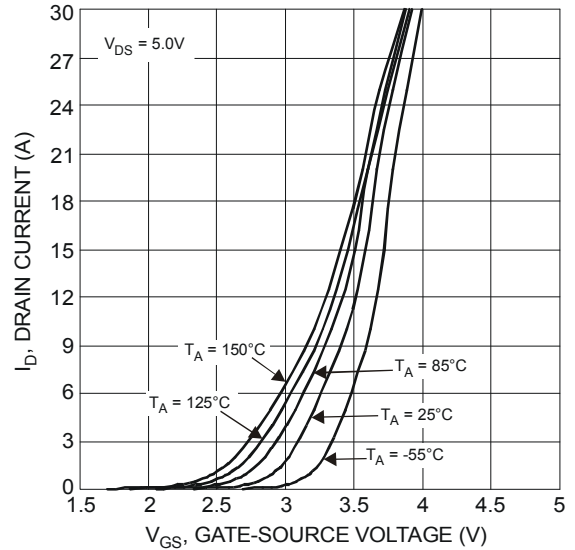


Figure 2 Typical Transfer Characteristics

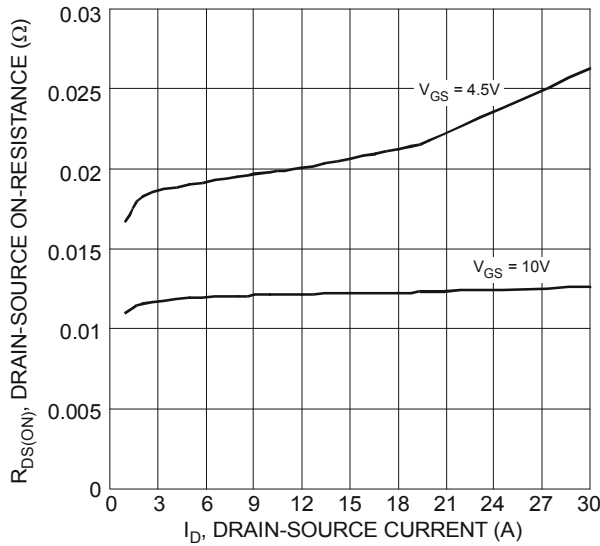


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

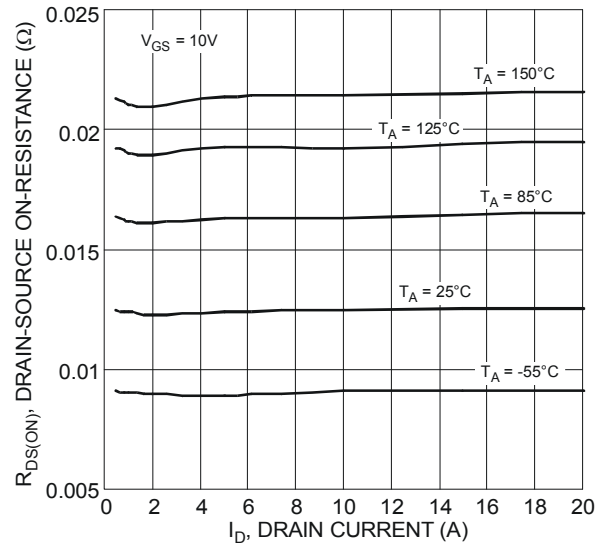


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

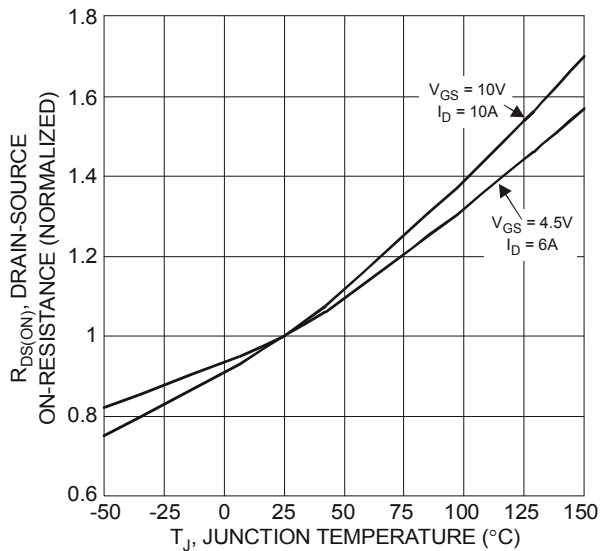


Figure 5 On-Resistance Variation with Temperature

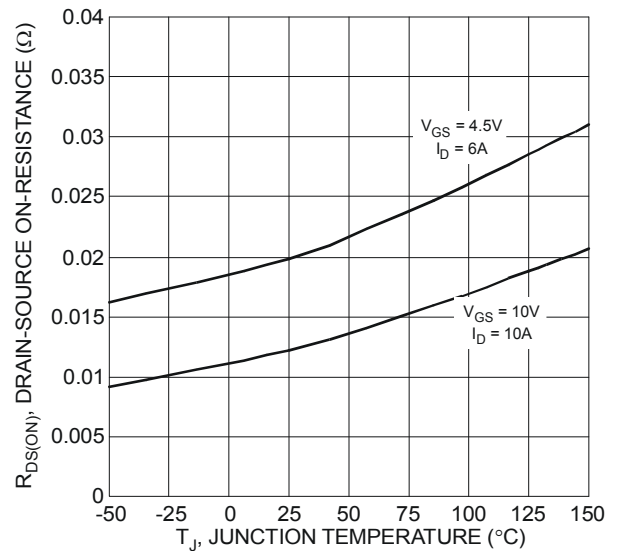


Figure 6 On-Resistance Variation with Temperature

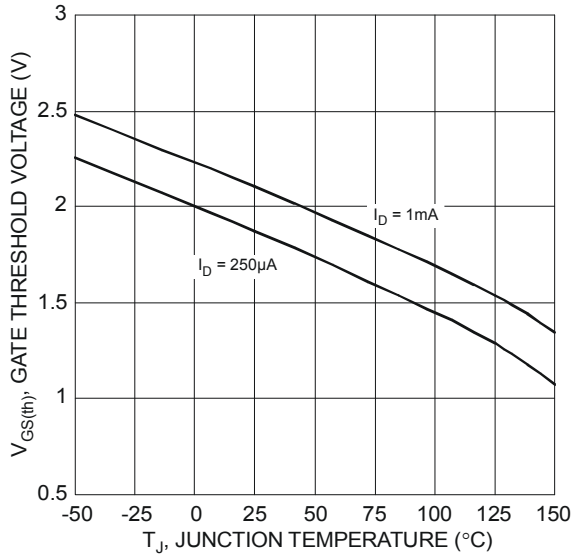


Figure 7 Gate Threshold Variation vs. Ambient Temperature

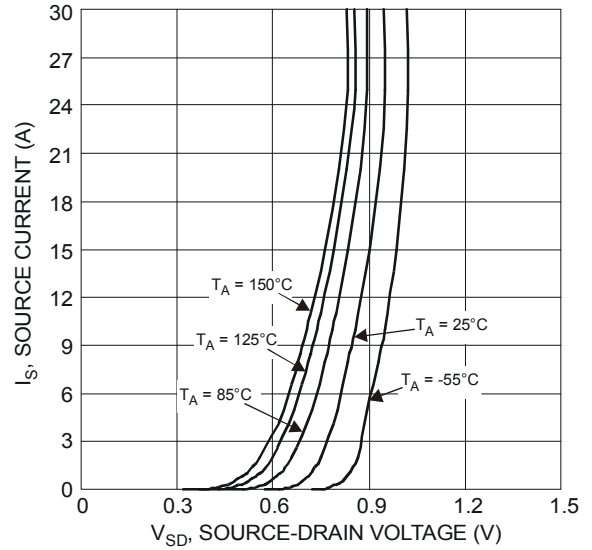


Figure 8 Diode Forward Voltage vs. Current

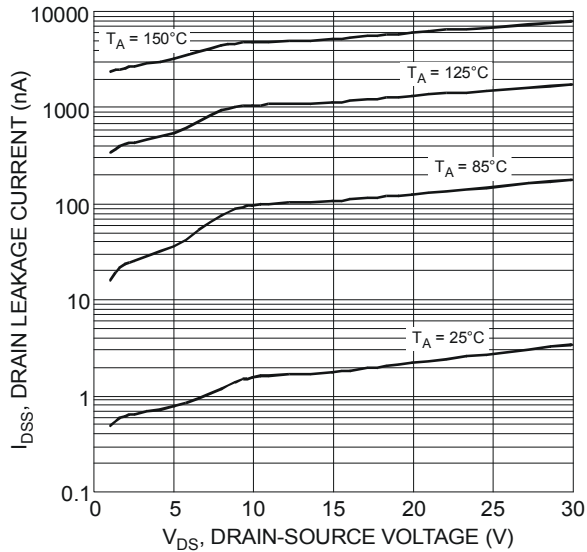


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

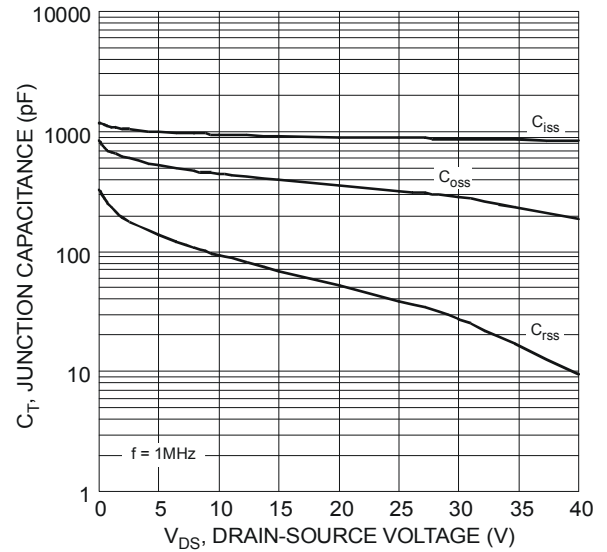


Figure 10 Typical Junction Capacitance

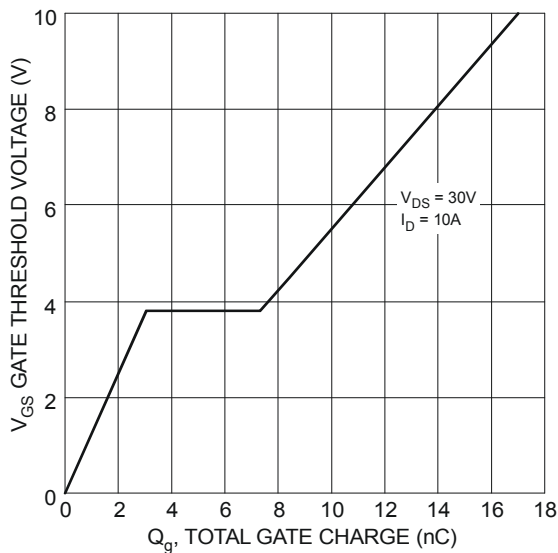


Figure 11 Gate Charge

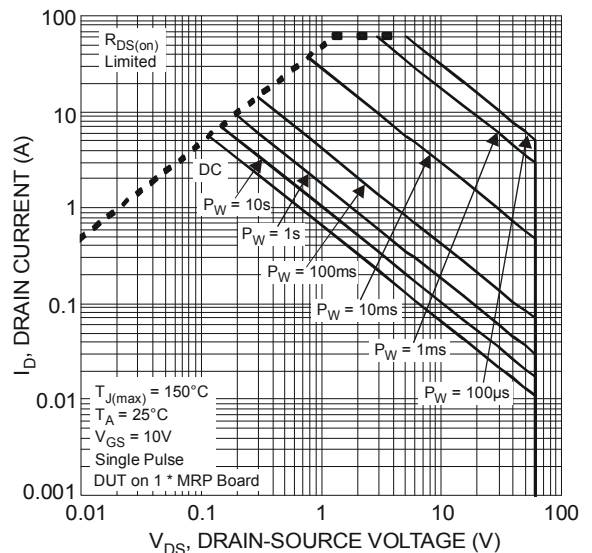


Figure 12 SOA, Safe Operation Area

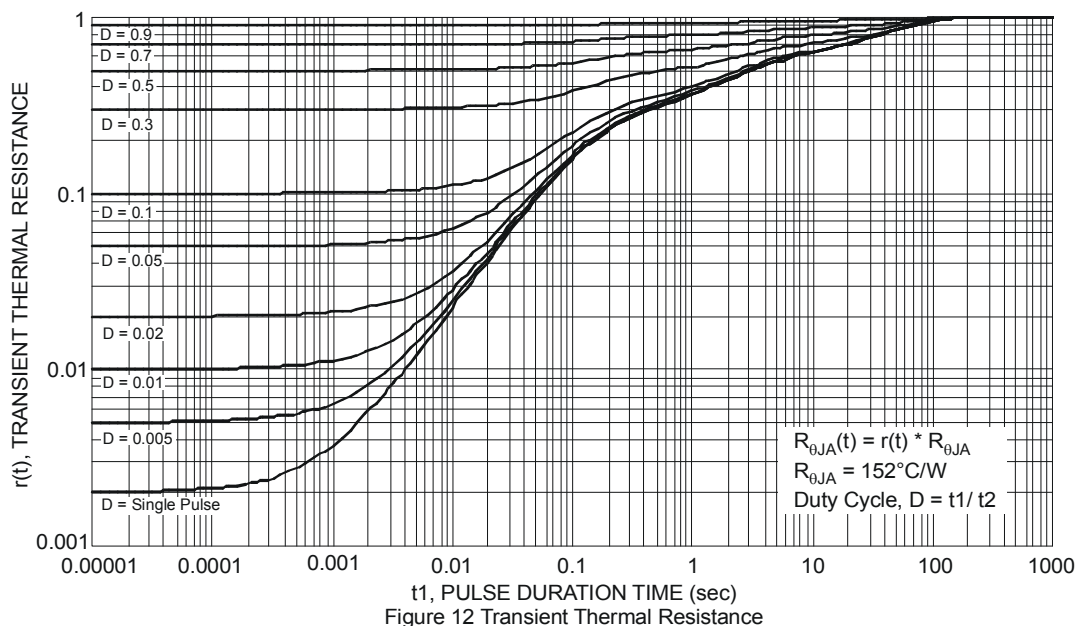
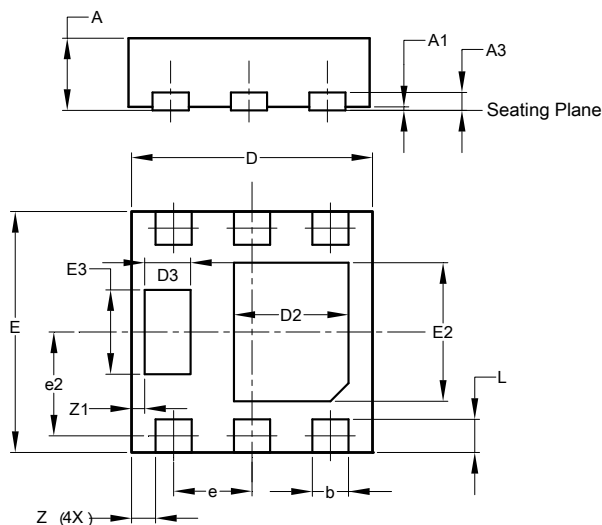


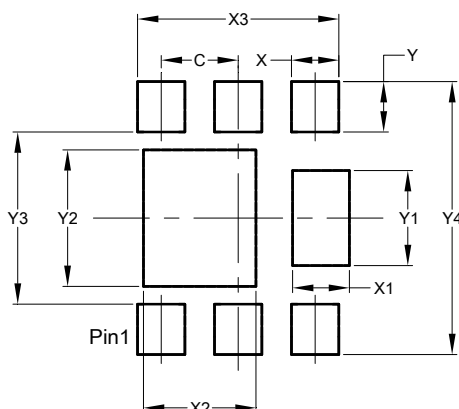
Figure 12 Transient Thermal Resistance

Package Outline Dimensions

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.


U-DFN2020-6			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D3	0.33	0.43	0.38
e	0.65 BSC		
e2	0.863 BSC		
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E3	0.65	0.75	0.70
L	0.225	0.325	0.275
Z	0.20 BSC		
Z1	0.110 BSC		
All Dimensions in mm			

Suggested Pad Layout

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.


Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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